# RENESAS BCR12PM-14LG

Triac Medium Power Use

> REJ03G1556-0100 Rev.1.00 Jul 06, 2007

# Features

- $I_{T (RMS)}$  : 12 A
- $V_{DRM}$  : 800 V (Tj = 125°C)
- I<sub>FGTI</sub>, I<sub>RGTI</sub>, I<sub>RGTIII</sub> : 30 mA
- Viso : 2000 V

- The Product guaranteed maximum junction temperature 150°C
- Insulated Type
- Planar Type
- UL Recognized: Yellow Card No. E223904

File No. E80271

# Outline



### Applications

Washing machine, inversion operation of capacitor motor, and other general controlling devices

### **Maximum Ratings**

Parameter	Symbol	Voltage class	Unit	Conditions
Faialletei	Symbol	14	Onic	
Repetitive peak off-state voltage <sup>Note1</sup>	V <sub>DRM</sub>	800	V	Tj = 125°C
		700	V	Tj = 150°C
Non-repetitive peak off-state voltage <sup>Note1</sup>	V <sub>DSM</sub>	840	V	

### BCR12PM-14LG

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	I <sub>T (RMS)</sub>	12	A	Commercial frequency, sine full wave 360° conduction, Tc = 93°C
Surge on-state current	I <sub>TSM</sub>	120	A	60Hz sinewave 1 full cycle, peak value, non-repetitive
I <sup>2</sup> t for fusing	l <sup>2</sup> t	60	A <sup>2</sup> s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	P <sub>GM</sub>	5	W	
Average gate power dissipation	P <sub>G (AV)</sub>	0.5	W	
Peak gate voltage	V <sub>GM</sub>	10	V	
Peak gate current	I <sub>GM</sub>	2	А	
Junction temperature	Tj	- 40 to +150	°C	
Storage temperature	Tstg	- 40 to +150	°C	
Mass	—	2.0	g	Typical value
Isolation voltage	Viso	2000	V	Ta = 25°C, AC 1 minute, T <sub>1</sub> • T <sub>2</sub> • G terminal to case

Notes: 1. Gate open.

# **Electrical Characteristics**

Parameter		Symbol	Min.	Тур.	Max.	Unit	Test conditions
Repetitive peak off-state current		I <sub>DRM</sub>	—	—	2.0	mA	Tj = 150°C, V <sub>DRM</sub> applied
On-state voltage		V <sub>TM</sub>	—	—	1.6	V	Tc = 25°C, I <sub>TM</sub> = 20 A,
_							Instantaneous measurement
Gate trigger voltage <sup>Note2</sup>	Ι	$V_{FGTI}$	—	—	1.5	V	$Tj = 25^{\circ}C, V_D = 6 V, R_L = 6 \Omega,$
	II	V <sub>RGTI</sub>	_	—	1.5	V	R <sub>G</sub> = 330 Ω
	III	V <sub>RGTIII</sub>	—	—	1.5	V	
Gate trigger current <sup>Note2</sup>	Ι	I <sub>FGTI</sub>	—	—	30	mA	$Tj = 25^{\circ}C, V_D = 6 V, R_L = 6 \Omega,$
	II	I <sub>RGTI</sub>	_	—	30	mA	R <sub>G</sub> = 330 Ω
	III	I <sub>RGTIII</sub>	_	_	30	mA	
Gate non-trigger voltage		V <sub>GD</sub>	0.2/0.1	—		V	$Tj = 125^{\circ}C/150^{\circ}C, V_D = 1/2 V_{DRM}$
Thermal resistance		R <sub>th (j-c)</sub>	—	—	4.0	°C/W	Junction to case <sup>Note3</sup>
Critical-rate of rise of off-state commutating voltage <sup>Note4</sup>		(dv/dt)c	10/1	—	—	V/µs	Tj = 125°C/150°C

Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

3. The contact thermal resistance Rth (c-f) in case of greasing is 0.5°C/W.

4. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

Test conditions	Commutating voltage and current waveforms (inductive load)		
1. Junction temperature Tj = 125°C/150°C	Supply Voltage → Time		
2. Rate of decay of on-state commutating current (di/dt)c = - 6.0 A/ms	Main Current → Time		
3. Peak off-state voltage $V_D = 400 \text{ V}$	Main Voltage → Time (dv/dt)c V <sub>D</sub>		

### **Performance Curves**



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# **Package Dimensions**



### Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Vinyl sack	100	Type name	BCR12PM-14LG
Lead form	Plastic Magazine (Tube)	50	Type name – Lead forming code	BCR12PM-14LG-A8

Note : Please confirm the specification about the shipping in detail.

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http://www.renesas.com

Refer to "http://www.renesas.com/en/network" for the latest and detailed information.

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